

# **ΒΑΣΙΚΕΣ ΕΞΙΣΩΣΕΙΣ ΗΛΕΚΤΡΟΝΙΚΗΣ ΙΙΙ**

### Πολυβάθμιοι ενισχυτές

$$A_v = \frac{e_{out}}{V_S} = \prod_{i=1}^n A_i = \frac{R_{in,1}}{R_{in,1} + R_S} \cdot \frac{R_{in,2}}{R_{in,2} + R_{out,1}} \cdot \dots \cdot \frac{R_L}{R_L + R_{out,n}}$$

Με  $n$  όμοιες βαθμίδες:  $\omega_{nL} = \frac{\omega_0}{\sqrt{2^{1/n-1}}}$ . Με  $n$  βαθμίδες με  $f_{Lj}$ ,  $j = 1, \dots, n$ :  $f_{nL} \approx 1.1 \sqrt{\sum_{j=1}^n f_{Lj}^2}$

Με  $n$  όμοιες βαθμίδες:  $\omega_{nH} = \omega_0 \sqrt{2^{1/n-1}}$ . Με  $n$  βαθμίδες με  $f_{Hj}$ ,  $j = 1, \dots, n$ :  $f_{nH} \approx \left(1.1 \sqrt{\sum_{j=1}^n f_{Hj}^2}\right)^{-1}$

#### Ζεύγος κοινού συλλέκτη - κοινής βάσης:

$$\frac{V_o}{V_{sig}} = \frac{1}{2} \left( \frac{R_{in}}{R_{in} + R_{sig}} \right) (g_m R_L) \quad R_{in} = 2r_\pi$$

$$f_{P1} = \frac{1}{2\pi \left( \frac{C_\pi}{2} + C_\mu \right) (R_{sig} \parallel 2r_\pi)} \quad f_{P2} = \frac{1}{2\pi C_\mu R_L} \quad f_H \cong \frac{1}{\sqrt{\frac{1}{f_{P1}^2} + \frac{1}{f_{P2}^2}}}$$

#### Ζεύγος κοινής πηγής - κοινής πύλης (κασκοδική συνδεσμολογία):

$$R_{out} = r_{o2} + [1 + (g_{m2} + g_{mb2}) r_{o2}] r_{o1} \quad A_v = -A_0^2 \frac{R_L}{R_L + A_0 r_0} \quad f_H \cong \frac{1}{2\pi \tau_H}$$

$$R_{gd1} = (1 + g_{m1} R_{d1}) R_{sig} + R_{d1} \quad \tau_H = R_{sig} [C_{gs1} + C_{gd1} (1 + g_{m1} R_{d1})] + R_{d1} (C_{gd1} + C_{db1} + C_{gs2}) + (R_L \parallel R_{out}) (C_L + C_{gd2})$$

#### Ζεύγος κοινού εκπομπού - κοινής βάσης (κασκοδική συνδεσμολογία):

$$A_M = -\frac{r_\pi}{r_\pi + r_x + R_{sig}} g_m (\beta r_0 \parallel R_L) \quad R_{c1} = r_{o1} \parallel \left[ r_{e2} \left( \frac{r_{o2} + R_L}{r_{o2} + R_L / (\beta_2 + 1)} \right) \right]$$

$$R'_{sig} = r_{\pi1} \parallel (r_{x1} + R_{sig}) \quad \tau_H = C_{\pi1} R_{\pi1} + C_{\mu1} R_{\mu1} + (C_{cs1} + C_{\pi2}) R_{c1} + (C_L + C_{cs2} + C_{\mu2}) (R_L \parallel R_{out})$$

$$R_{\mu1} = R'_{sig} (1 + g_{m1} R_{c1}) + R_{c1} \quad f_H \cong \frac{1}{2\pi \tau_H}$$

#### Τελεστικός ενισχυτής MOS δύο βαθμίδων:

$$A_v = -g_{m1} (r_{ds2} \parallel r_{ds4}) \quad g_{m1} = \sqrt{2\mu_p C_{ox} \left( \frac{W}{L} \right)_1 I_{D1}} = \sqrt{2\mu_p C_{ox} \left( \frac{W}{L} \right)_1 \frac{I_{bias}}{2}}$$

$$R_B = \frac{2}{\sqrt{2\mu_n C_{ox} (W/L)_{12}} I_B} \left( \sqrt{\frac{(W/L)_{12}}{(W/L)_{13}}} - 1 \right)$$

$$g_{m12} = \frac{2}{R_B} \left( \sqrt{\frac{(W/L)_{12}}{(W/L)_{13}}} - 1 \right) \quad g_{mi} = g_{m12} \sqrt{\frac{I_{Di} (W/L)_i}{I_B (W/L)_{12}}} \quad g_{mi} = g_{m12} \sqrt{\frac{\mu_p I_{Di} (W/L)_i}{\mu_n I_B (W/L)_{12}}}$$

$$C_1 = C_{gd4} + C_{db4} + C_{gd2} + C_{gs6} \quad C_2 = C_{db6} + C_{db7} + C_{gd7} + C_L$$

$$\omega_Z = \frac{G_{m2}}{C_C} \quad \omega_{P1} = \frac{1}{C_1 R_1 + C_2 R_2 + C_C (G_{m2} R_2 R_1 + R_1 + R_2)} \cong \frac{1}{R_1 C_C G_{m2} R_2}$$

$$\omega_{P2} = \frac{G_{m2} C_C}{C_1 C_2 + C_C (C_1 + C_2)} \quad \omega_t = (G_{m1} R_1 G_{m2} R_2) \omega_{P1} \quad \text{Επιλογή } C_C \text{ ώστε } \omega_t < \omega_Z < \omega_{P2}$$

$$PSRR = g_{mN} (r_{oP} \parallel r_{oN}) \quad SR \equiv \left. \frac{dV_{out}}{dt} \right|_{\max} = \frac{I_{SS}}{C_L}$$

$$GB = A_v(0) \cdot |p_1| = (g_{m1} g_{m2} R_I R_{II}) \cdot \left( \frac{1}{g_{m2} R_I R_{II} C_C} \right) = \frac{g_{m1}}{C_C}$$

$$PM = \text{Arg}[AB] = \pm 180^\circ - \arctan \left( \frac{\omega}{|p_1|} \right) - \arctan \left( \frac{\omega}{|p_2|} \right) - \arctan \left( \frac{\omega}{Z} \right)$$

Για περιθώριο φάσης (PM)  $45^\circ$  και  $Z \geq 10 \cdot GB$ :  $|p_2| \geq 1.22 \cdot GB$

Για περιθώριο φάσης (PM)  $60^\circ$  και  $Z \geq 10 \cdot GB$ :  $|p_2| \geq 2.22 \cdot GB$

$$Z = \frac{1}{C_C \left( \frac{1}{g_{m2}} - R_Z \right)}$$

**Τελεστικός ενισχυτής με είσοδο n-MOS**

$$\max(V_{in}) = V_{DD} - \sqrt{\frac{I_5}{\beta_3}} - \max(|V_{T03}|) + \min(V_{T01}) \quad \min(V_{in}) = V_{SS} + \sqrt{\frac{I_5}{\beta_1}} + \max(V_{T01}) + V_{DS5sat} \quad V_{DS5sat} = \sqrt{\frac{2I_{DS}}{\beta}}$$

**Τελεστικός ενισχυτής με είσοδο p-MOS**

$$\max(V_{in}) = V_{DD} - \sqrt{\frac{I_5}{\beta_1}} - V_{DS5sat} - \max(|V_{T01}|) \quad \min(V_{in}) = V_{SS} + \sqrt{\frac{I_5}{\beta_3}} + \max(V_{T03}) - \min(|V_{T01}|)$$

**Σχεδίαση τελεστικού ενισχυτή με είσοδο n-MOS**

$$\begin{aligned} SR &= \frac{I_5}{C_C} & A_{v1} &= \frac{-g_{m1}}{g_{ds2} + g_{ds4}} = \frac{-2g_{m1}}{I_5 \cdot (\lambda_2 + \lambda_4)} & A_{v2} &= \frac{-g_{m6}}{g_{ds6} + g_{ds7}} = \frac{-g_{m6}}{I_6 \cdot (\lambda_6 + \lambda_7)} \\ GB &= \frac{g_{m1}}{C_C} & p_2 &= \frac{-g_{m6}}{C_L} \quad Z = \frac{g_{m6}}{C_C} & \beta &= k' \frac{W}{L} \cong \mu_0 C_{ox} \frac{W}{L} (A/V^2) \\ C_C &> 0.22C_L & I_5 &= SR \cdot C_C \quad S_3 = \left(\frac{W}{L}\right)_3 = \frac{I_5}{k'_3 [V_{DD} - \max(V_{in}) - \max(|V_{T03}|) + \min(V_{T01})]^2} \\ \frac{g_{m3}}{2C_{gs3}} &> 10 \cdot GB & g_{m1} &= GB \cdot C_C \implies S_1 = S_2 = \frac{g_{m2}^2}{k_2 I_5} \\ V_{DS5sat} &= \min(V_{in}) - V_{SS} - \sqrt{\frac{I_5}{\beta_1}} - \max(V_{T01}) \geq 100\text{mV} & S_5 &= \frac{2I_5}{k'_5 V_{DS5sat}^2} \\ g_{m6} &= 2.2g_{m2} (C_L/C_C) \quad S_6 = S_4 \frac{g_{m6}}{g_{m4}} \quad I_6 = \frac{g_{m6}^2}{2k'_6 S_6} \\ S_6 &= \frac{g_{m6}}{k'_6 V_{DS6sat}} & V_{DS6} &= \min(V_{DS6}) = V_{DS6sat} = V_{DD} - \max(V_{out}) \quad S_7 = S_5 \frac{I_6}{I_5} \\ A_v &= \frac{2g_{m2}g_{m6}}{I_5 (\lambda_2 + \lambda_4) I_6 (\lambda_6 + \lambda_7)} & P_{diss} &= (I_5 + I_6) \cdot (V_{DD} + |V_{SS}|) \end{aligned}$$

**Κυκλώματα ανόρθωσης**

<b>Zener diode:</b>	$V_Z = V_{Z0} + r_Z \cdot I_Z$
<b>Ημιανορθωτής:</b>	$P_{DC} = I_{DC}^2 R = \frac{I_m^2}{\pi^2} R \quad P_{AC} = I_{rms}^2 R = \frac{I_m^2}{4} R \quad n = \frac{P_{DC}}{P_{AC}} 100\% = 40.6\% \quad r = \frac{\sqrt{I_{rms}^2 - I_{DC}^2}}{I_{DC}} 100\% = 121\%$
<b>Πλήρης ανορθωτής:</b>	$P_{DC} = I_{DC}^2 R = \frac{4I_m^2}{\pi^2} R \quad P_{AC} = I_{rms}^2 R = \frac{I_m^2}{2} R \quad n = \frac{P_{DC}}{P_{AC}} 100\% = 81.2\% \quad r = \frac{\sqrt{I_{rms}^2 - I_{DC}^2}}{I_{DC}} 100\% = 48\%$
<b>Ημιανορθωτής με φίλτρο πυκνωτή:</b>	$V_{DC} \equiv V_o = V_p - \frac{1}{2}V_r \quad i_{D,av} = I_L \left(1 + \pi \sqrt{2V_p/V_r}\right) \quad i_{D,max} = I_L \left(1 + 2\pi \sqrt{2V_p/V_r}\right)$ $V_r = \frac{V_p}{fCR} = \frac{I_L}{fC} \quad r = \frac{V_{AC,rms}}{V_{DC}} = \frac{V_r}{2\sqrt{3}V_{DC}} \approx \frac{1}{2\sqrt{3}fCR}$
<b>Πλήρης ανορθωτής με φίλτρο πυκνωτή:</b>	$V_r = \frac{V_p}{2fCR} \quad i_{D,av} = I_L \left(1 + \pi \sqrt{V_p/2V_r}\right) \quad i_{D,max} = I_L \left(1 + 2\pi \sqrt{V_p/2V_r}\right)$ $r = \frac{V_{AC,rms}}{V_{DC}} = \frac{V_r}{2\sqrt{3}V_{DC}} \approx \frac{1}{4\sqrt{3}fCR}$

### Κυκλώματα αναφοράς

#### Πηγή Widlar:

$$V_T \cdot \ln \left( \frac{I_{in}}{I_{out}} \right) = I_{out} \cdot R_2 \quad I_{out} R_2 + \sqrt{\frac{2I_{out}}{k' (W/L)_2}} - V_{ov1} = 0 \quad \sqrt{I_{out}} = \frac{-\sqrt{\frac{2}{k' (W/L)_2}} - \sqrt{\frac{2}{k' (W/L)_2} + 4R_2 V_{ov1}}}{2R_2}$$

#### Πηγή μεγίστου ρεύματος:

$$I_{out} = I_{in} \exp \left( -\frac{I_{in} R}{V_T} \right) \quad R = \frac{V_T}{I_{in}} \ln \left( \frac{I_{in}}{I_{out}} \right) \quad I_D = \frac{W}{L} I_t \exp \left( \frac{V_{GS} - V_t}{nV_T} \right) \cdot \left[ 1 - \exp \left( -\frac{V_{DS}}{V_T} \right) \right]$$

$$I_{out} \simeq \frac{W}{L} I_t \exp \left( \frac{V_{GS2} - V_t}{nV_T} \right) \simeq I_{in} \exp \left( -\frac{I_{in} R}{nV_T} \right) \quad I_{out} = \frac{k'}{2} \left( \frac{W}{L} \right)_2 V_{ov2}^2 = \frac{k'}{2} \left( \frac{W}{L} \right)_2 (V_{ov1} - I_{in} R)^2$$

$$S_{V_{sup}}^{I_{out}} = \frac{V_{sup}}{I_{out}} \cdot \frac{\partial I_{out}}{\partial V_{sup}} \quad S_{V_{sup}}^{I_{out}} = \left( \frac{1}{1 + \frac{I_{out} R_2}{V_T}} \right) \cdot \frac{V_{CC}}{I_{in}} \cdot \frac{\partial I_{in}}{\partial V_{CC}} = \left( \frac{1}{1 + \frac{I_{out} R_2}{V_T}} \right) S_{V_{CC}}^{I_{in}}$$